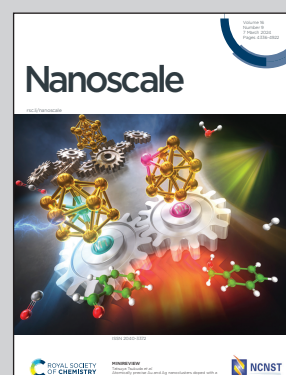


Showcasing research from Professor Hi-Deok Lee's Microelectronic Device And Sensor (MIDAS) laboratory, School of Electronics Engineering, University of Chungnam National University, Daejeon, Korea.

Effects of thermal annealing on analog resistive switching behavior in bilayer  $\text{HfO}_2/\text{ZnO}$  synaptic devices: the role of ZnO grain boundaries

The performance of  $\text{HfO}_2/\text{ZnO}$  synaptic devices improved through thermal annealing. The annealing process made ZnO more crystallized and its change in grain boundaries affected the resistive switching behaviour and long-term potentiation/depression properties which are important for neural networks.

As featured in:



See Hi-Deok Lee, Hyuk-Min Kwon *et al.*, *Nanoscale*, 2024, **16**, 4609.